

CLAIMS:

1. A filter (3) provided with field effect (FET) capacitors (M1-32; M'1-32) arranged for controlling their respective capacity values, each such FET capacitor (M1-32; M'1-32) having a source (S) and a drain (D), characterised in that the source (S) and the drain (D) of each FET capacitor (M1-32; M'1-32) are coupled to one another.
2. The filter (3) according to claim 1, characterised in that each FET capacitor (M1-32; M'1-32) has a control input (G1-32; G'1-32) for voltage dependent capacity value control.
3. The filter (3) according to claim 1 or 2, characterised in that the filter (3) is provided with control means (Contr.) coupled to FET capacitor control inputs (G1-32; G'1-32).
4. The filter (3) according to one of the claims 1-3, characterised in that the FET capacitors (M1-32; M'1-32) are split in equally controlled pairs of FET capacitors (M1-32; M'1-32).
5. The filter (3) according to one of the claims 1-4, characterised in that the filter (3) is built up as a symmetrical filter (3) having a symmetrical input (5) and a symmetrical output (6).
6. The filter (3) according to one of the claims 1-5, characterised in that two or more of the FET capacitors (M1-32; M'1-32) are connected in series.
7. The filter (3) according to one of the claims 1-6, characterised in that the FET capacitors (M1-32; M'1-32) are metal oxide semiconductor (MOSFET) capacitors (M1-32; M'1-32).

8. A transmitter, receiver, or transceiver having a filter (3) according to one of the claims 1-7, which filter (3) is provided with field effect (FET) capacitors (M1-32; M'1-32) arranged for controlling their respective capacity values, each such FET capacitor (M1-32; M'1-32) having a source (S) and a drain (D), characterised in that the source (S) and the
- 5 drain (D) of each FET capacitor (M1-32; M'1-32) are coupled to one another.